SHI LING® 浙江世 菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

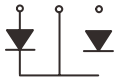
Specifcation of products

MURP200100CIT26B

ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

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Thermal Characteristics

Symbol	Parameter	Conditions	Values			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)}$	Thermal Resistance	Junction to Case	-	-	0.10	℃/W

Electrical Characteristics @ T_j=25℃(unlessotherwise specified)

Symbol	Parameter	Conditions	Values			Unit
			Min.	Typ.	Max.	
V_R	Cathode Anode Breakdown Voltage	I_R= 100uA			-	
V_{FM}	Maximum Forward Voltage	I_{FM}= 400A, T_c= 25℃ I_{FM}= 400A, T_c =100℃			1.1 0.8	
I_{RRM}	Repetitive Peak Reverse Current	T_C= 100℃ , V_{RRM} applied				
t_{rr}	Reverse RecoveryTime	I_{FM}= 200A, V_R= 150V di/dt=-100A/us				

Package Outlines

Unit:mm

Performance Curves

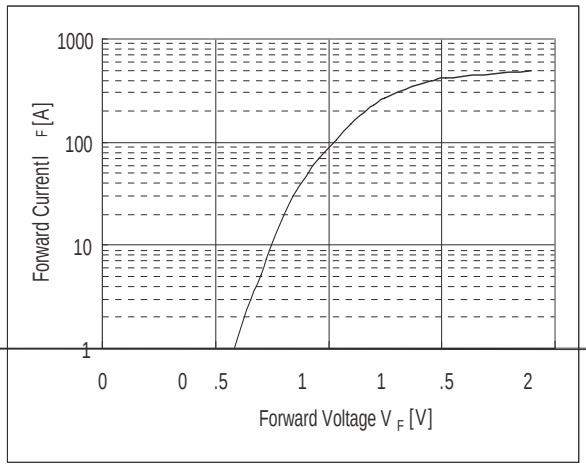


Fig. 1 : Typical Forward Voltage Drop vs. Instantaneous Forward Current

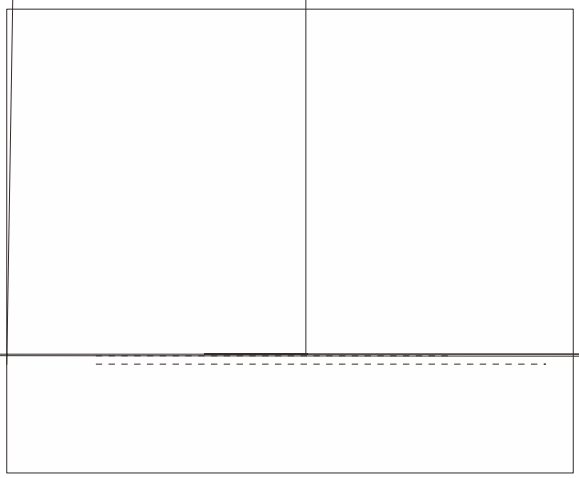


Fig. 2 : Typical Reverse Recovery Time vs. -di/dt